

**DESCRIPTION**

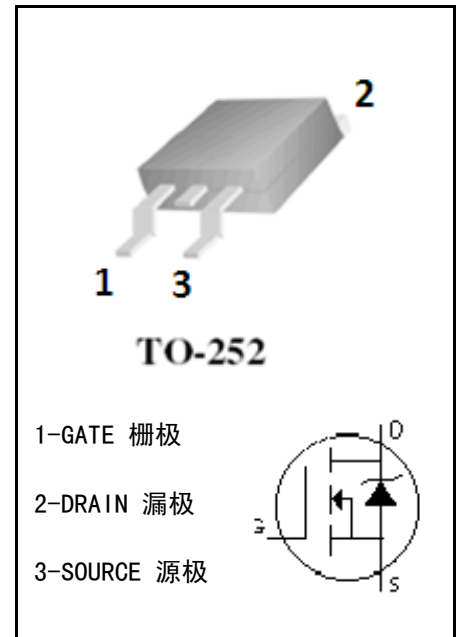
- ELECTRONIC BALLAST
- ELECTRONIC TRANSFORMER
- SWITCH MODE POWER SUPPLY

**FEATURES:**

- LOW THERMAL RESISTANCE
- HIGH INPUT RESISTANCE
- FAST SWITCHING
- ROHS COMPLIANT

**MAXIMUM RATINGS (T<sub>c</sub>=25°C)**

PARAMETER	SYMBOL	VALUE	UNIT
Drain-source Voltage	VDS	650	V
gate-source Voltage	VGS	±25	V
Continuous Drain Current (T <sub>C</sub> =25°C)	ID	11	A
Drain Current-Pulsed	IDM	44	A
Total Dissipation	PD	80	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55-150	°C
Single Pulse Avalanche Energy (I <sub>AS</sub> =11A)	EAS	210	mJ

**MECHANICAL**

**ELECTRONIC CHARACTERISTICS (T<sub>c</sub>=25°C)**

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Drain-source Breakdown Voltage	BVDSS	VGS=0V, ID=250uA	650		V
Gate Threshold Voltage	VGS (TH)	VGS=VDS, ID=250 μ A	2	4	V
Drain-source Leakage Current	IDSS	VDS=650V, VGS=0V		1	uA
Drain-Source Diode Forward Voltage	VSD	VGS=0V, IS=11A		1.5	V
Gate-body Leakage Current (VDS = 0)	IGSS	VGS=±25V		±0.1	uA
Forward Transconductance	gfs	Vds=10V Id=5.5A	4		S
Static Drain-source On Resistance	RDS (ON)	VGS=10V, ID=5.5A		0.42	Ω
Thermal Resistance Junction-case	RthJ-c			1.5	°C/W

**■ DYNAMIC CHARACTERISTICS (T<sub>c</sub>=25°C)**

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz	-	620	-	pF
output Capacitance	C <sub>oss</sub>		-	260	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	6	-	pF

**■ SWITCHING CHARACTERISTICS (T<sub>c</sub>=25°C)**

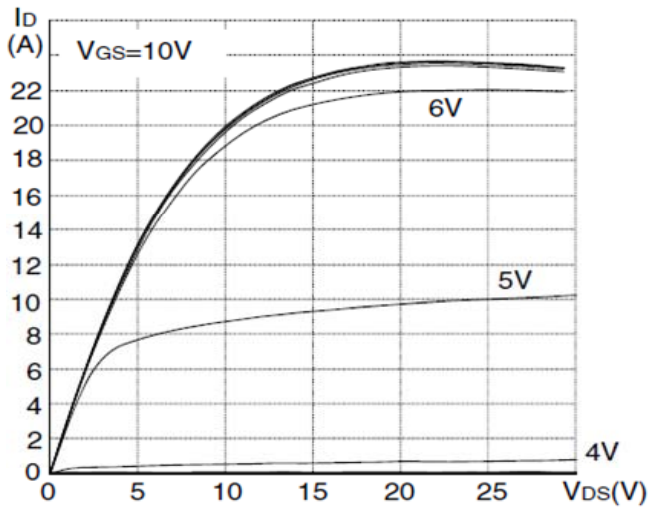
CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =300V, I <sub>D</sub> =5.5A, R <sub>G</sub> =25Ω, V <sub>GS</sub> =10V	-	3	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	8	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	30	-	ns
Turn-Off Rise Time	t <sub>f</sub>		-	10	-	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =480V, I <sub>D</sub> =11A, V <sub>GS</sub> =10V	-	27	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	14	-	nC

**■ DRAIN-SOURCE DIODE MAXIMUM RATINGS AND CHARACTERISTICS (T<sub>c</sub>=25°C)**

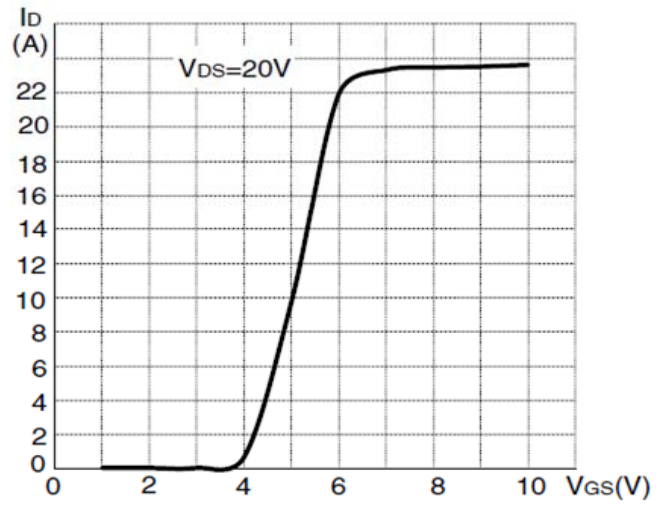
CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Max. Diode Forward Current	I <sub>s</sub>		-	-	11	A
Max. Pulsed Forward Current	I <sub>SM</sub>		-	-	44	A
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =11A	-	-	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =11A, dI <sub>F</sub> /dt=100A/μs, V <sub>DD</sub> =100V	-	230	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>		-	2	-	μC



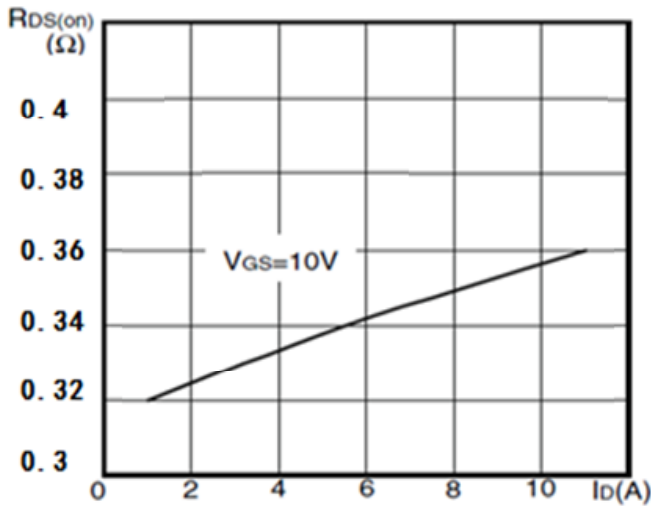
CHARACTERISTICS CURVE



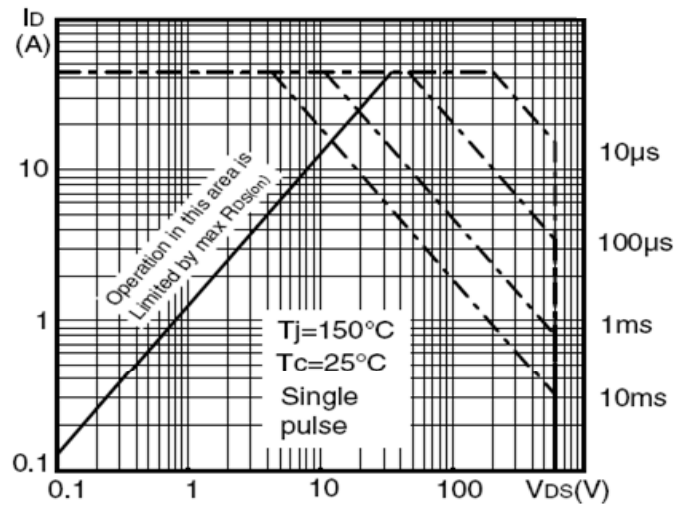
Output Characteristic



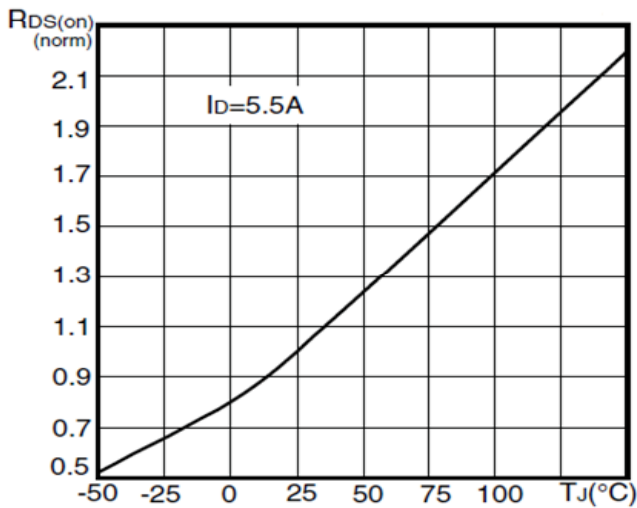
Transfer Characteristic



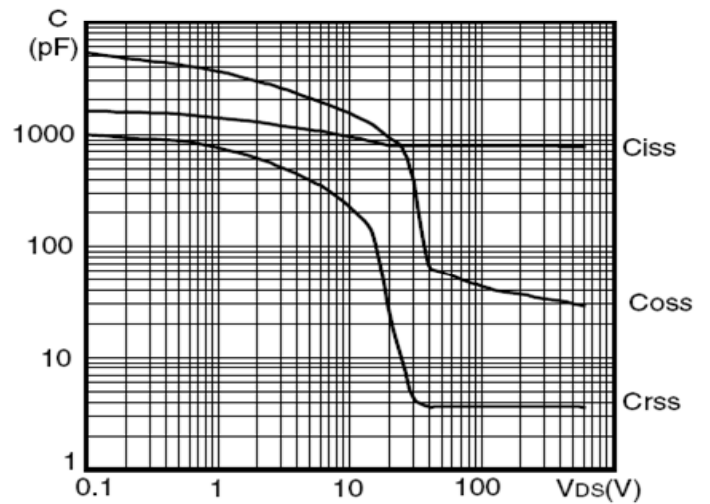
On Resistance Vs Drain Current



Safe Operating Area



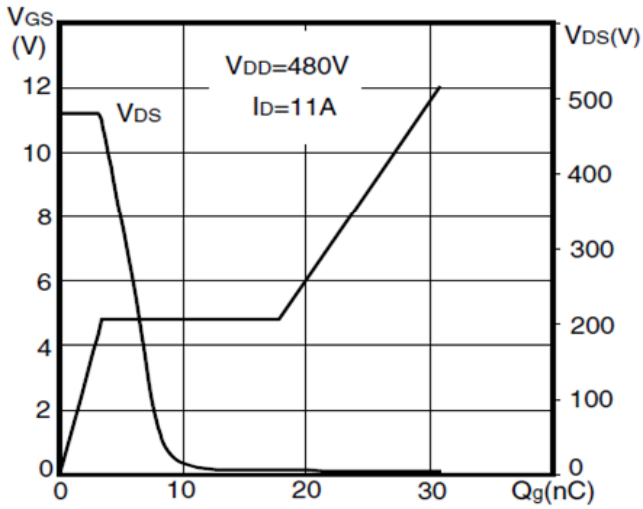
On Resistance Vs Junction Temperature



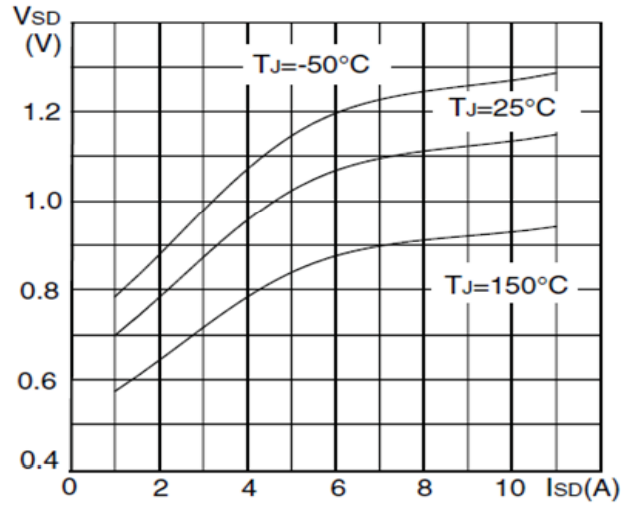
Capacitance



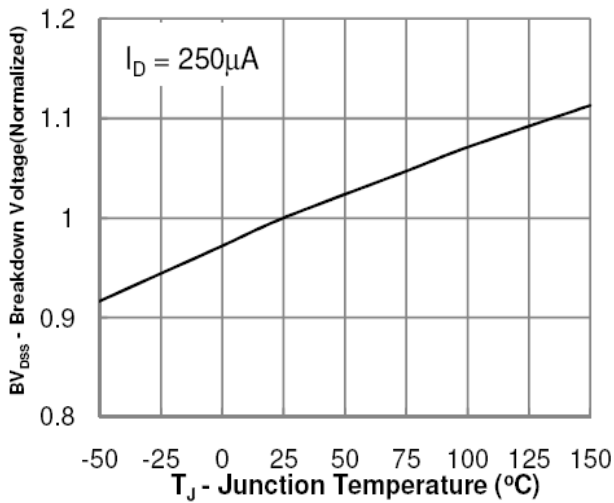
■ CHARACTERISTICS CURVE



Gate Charge Waveform



Source-Drain Diode Forward Voltage



Breakdown Voltage Vs Junction Temperature

**TO-252 MECHANICAL DATA**

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	2.10		2.50	E	5.80		6.30
B	0.80		1.25	e1	2.25	2.30	2.35
b	0.50		0.85	e2	4.45		4.75
b1	0.50		0.90	L1	9.50		10.20
b2	0.45		0.60	L2	0.90		1.45
C	0.45		0.60	L3	0.60		1.10
D	6.35		6.75	K	-0.1		0.10
D1	5.10		5.50				

